

Form PTO 1449 U.S. Department of Commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER HIRA.0217	SERIAL NUMBER 10/565.624 To be Assigned
	APPLICANT SUDA et al.	
	FILING DATE Concurrently Herewith	GROUP

U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
	5,900,648	5/4/99	Harris et al.			3/28/97

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						Yes	No
	2000-150792	11/11/98	Japan			Abstract	X
	2001-094099	9/21/99	Japan			Abstract	X
	2002-246594	12/21/2001	Japan			Abstract	X
	FR 2 707 425	7/9/93	France			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

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	James Kolodzey et al., "Electrical Conduction and Dielectric Breakdown in Aluminum Oxide Insulators on Silicon", IEEE Transactions on Electron Devices., Vol. 47, No. 1, January 2000, pp. 121-128
	N. Onojima et al., "Heteroepitaxial Growth of Insulating AlN on 6H-SiC by MBE", Materials Science Forum Vols. 389-393, (2002), pp. 1457-1460
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